

CMOS MSI

Quad R-S Latches

MC14043B, MC14044B

The MC14043B and MC14044B quad R–S latches are constructed with MOS P–Channel and N–Channel enhancement mode devices in a single monolithic structure. Each latch has an independent Q output and set and reset inputs. The Q outputs are gated through three–state buffers having a common enable input. The outputs are enabled with a logical "1" or high on the enable input; a logical "0" or low disconnects the latch from the Q outputs, resulting in an open circuit at the Q outputs.

Features

- Double Diode Input Protection
- Three–State Outputs with Common Enable
- Outputs Capable of Driving Two Low–power TTL Loads or One Low–Power Schottky TTL Load Over the Rated Temperature Range
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient)	-0.5 to V _{DD} + 0.5	V
I _{in} , I _{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P _D	Power Dissipation, per Package (Note 1)	500	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

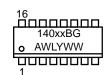
1. Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}.$

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



MARKING DIAGRAM



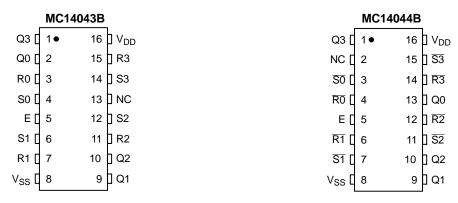
xx = Specific Device Code A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb-Free Indicator

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

PIN ASSIGNMENT



NC = NO CONNECTION

Figure 1.

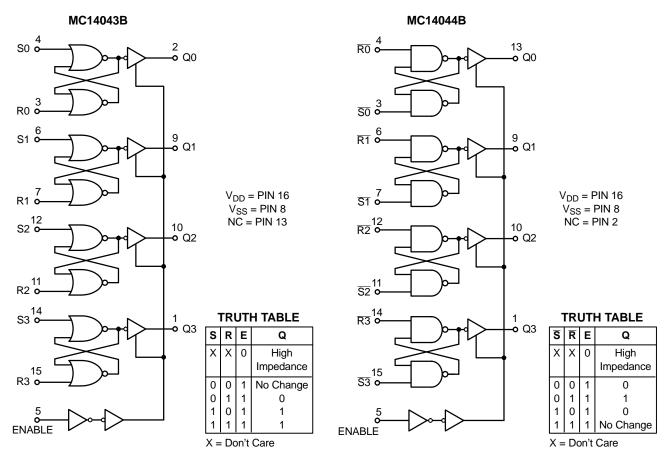


Figure 2.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

				- 5	5°C		25°C		125	5°C	
Characteristic		Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
V _{in} = 0 or V _{DD}	"1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage ($V_O = 4.5 \text{ or } 0.5 \text{ Vdc}$) ($V_O = 9.0 \text{ or } 1.0 \text{ Vdc}$) ($V_O = 13.5 \text{ or } 1.5 \text{ Vdc}$)	"0" Level	V _{IL}	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V _{IH}	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	Vdc
Output Drive Current (V _{OH} = 2.5 Vdc) (V _{OH} = 4.6 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc)	Source	ІОН	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - -	-1.7 -0.36 -0.9 -2.4	- - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current		I _{in}	15	_	±0.1	_	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V _{in} = 0)		C _{in}	1	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package)		I _{DD}	5.0 10 15	- - -	1.0 2.0 4.0	- - -	0.002 0.004 0.006	1.0 2.0 4.0	- - -	30 60 120	μAdc
Total Supply Current (Note (Dynamic plus Quiesce Per Package) (C _L = 50 pF on all output buffers switching)	nt,	I _T	5.0 10 15			$I_{T} = (1$.58 μΑ/kHz) .15 μΑ/kHz) .73 μΑ/kHz)	f + I _{DD}			μAdc
Three-State Output Leaka Current	ge	I _{TL}	15	-	±0.1	-	±0.0001	±0.1	-	±3.0	μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μA (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.004.

The formulas given are for the typical characteristics only at 25°C.
 To calculate total supply current at loads other than 50 pF:

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$)

Characteristic	Symbol	V _{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) C_L + 32.5 \text{ ns}$ $t_{TLH} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{TLH} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	t _{TLH}	5.0 10 15	- - -	100 50 40	200 100 80	ns
Output Fall Time $t_{THL} = (1.35 \text{ ns/pF}) C_L + 32.5 \text{ ns}$ $t_{THL} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{THL} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	t _{THL}	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH} = (0.90 \text{ ns/pF}) C_L + 130 \text{ ns}$ $t_{PLH} = (0.36 \text{ ns/pF}) C_L + 57 \text{ ns}$ $t_{PLH} = (0.26 \text{ ns/pF}) C_L + 47 \text{ ns}$	t _{PLH}	5.0 10 15	- - -	175 75 60	350 175 120	ns
t_{PHL} = (0.90 ns/pF) C_L + 130 ns t_{PHL} = (0.90 ns/pF) C_L + 57 ns t_{PHL} = (0.26 ns/pF) C_L + 47 ns	t _{PHL}	5.0 10 15	- - -	175 75 60	350 175 120	ns
Set, Set Pulse Width	t _W	5.0 10 15	200 100 70	80 40 30	- - -	ns
Reset, Reset Pulse Width	t _W	5.0 10 15	200 100 70	80 40 30	- - -	ns
Three-State Enable/Disable Delay	t _{PLZ} , t _{PHZ} , t _{PZL} , t _{PZH}	5.0 10 15	- - -	150 80 55	300 160 110	ns

AC WAVEFORMS

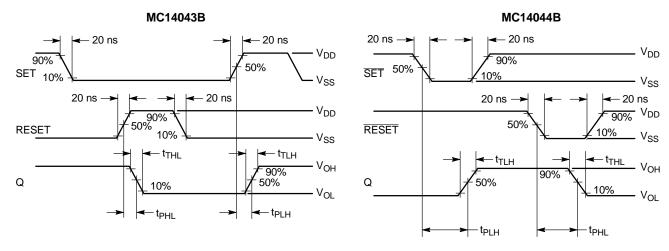


Figure 3.

^{5.} The formulas given are for the typical characteristics only at 25°C.6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

THREE-STATE ENABLE/DISABLE DELAYS

Set, Reset, Enable, and Switch Conditions for 3-State Tests

					MC14043B		MC14	044B
Test	Enable	S1	S2	Q	S	R	<u>s</u>	R
t _{PZH}		Open	Closed	Α	V_{DD}	V_{SS}	V_{SS}	V_{DD}
t _{PZL}		Closed	Open	В	V_{SS}	V_{DD}	V_{DD}	V_{SS}
t _{PHZ}	~	Open	Closed	Α	V_{DD}	V_{SS}	V_{SS}	V_{DD}
t _{PLZ}	~	Closed	Open	В	V_{SS}	V_{DD}	V_{DD}	V_{SS}

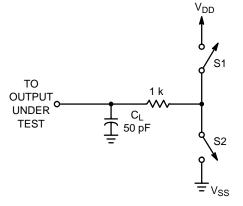


Figure 4.

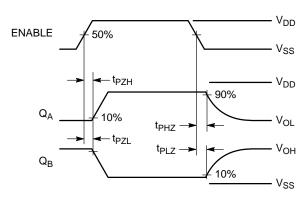


Figure 5.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC14043BDG	SOIC-16 (Pb-Free)	48 Units / Rail
NLV14043BDG*	SOIC-16 (Pb-Free)	48 Units / Rail
MC14043BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14043BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel

MC14044BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14044BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14044BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.





SOIC-16 CASE 751B-05 **ISSUE K**

DATE 29 DEC 2006

- NOTES:

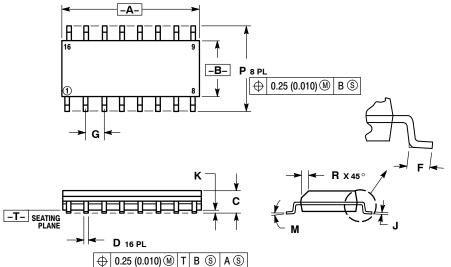
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD ENGREPHING.

- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES				
DIM	MIN	MIN MAX		MIN MAX MIN		MAX	
Α	9.80	10.00	0.386	0.393			
В	3.80	4.00	0.150	0.157			
С	1.35	1.75	0.054	0.068			
D	0.35	0.49	0.014	0.019			
F	0.40	1.25	0.016	0.049			
G	1.27	BSC	0.050 BSC				
J	0.19	0.25	0.008	0.009			
K	0.10	0.25	0.004	0.009			
M	0°	7°	0°	7°			
P	5.80	6.20	0.229	0.244			
R	0.25	0.50	0.010	0.019			



2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION	2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION ANODE CATHODE CATHODE CATHODE ANODE NO CONNECTION	2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3	2. 3. 4. 5. 6. 7. 8. 9.	COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 COLLECTOR, #4 BASE, #4 EMITTER, #4 BASE, #3	1	
12.	EMITTER BASE		CATHODE CATHODE	12.		12.		BECOM	MMENDED
13. 14.	COLLECTOR	13.	NO CONNECTION	13.	COLLECTOR, #4 BASE, #4	13. 14.	BASE, #2 EMITTER, #2		
15.	EMITTER		ANODE		EMITTER, #4	15.	BASE, #1	SOLDERING	G FOOTPRINT*
16.			CATHODE		COLLECTOR, #4		EMITTER, #1		8X
	002220.0		0,111002		0022201011,#1			L	6.40
STYLE 5:		STYLE 6:		STYLE 7:					0.40
	DRAIN, DYE #1		CATHODE		SOURCE N-CH				16X 1.12 <
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	T)			
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPU			1	16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	•,	1	<i>'</i> ==	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)	_		
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU	T)	16X		
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU	T)	0.58 ^{_1}		
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH				<u> </u>
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU		-		_
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3		ANODE	12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2	13.		13.	GATE N-CH	_			
14.	SOURCE, #2		ANODE	14.	COMMON DRAIN (OUTPU				. ☐ ↓ PITCH
15.	GATE, #1		ANODE	15.	COMMON DRAIN (OUTPU	1)			
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								8	9 + +

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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